April 2010

FAN6206 Highly Integrated Dual-Channel Synchronous Rectification Controller for Dual-Forward Converter

Features

SEMICONDUCTOR

- Highly Integrated Dual-Channel SR Controller
- Receives Synchronized Driving Signal from the Primary Side
- Internal Linear-Predict Timing Control for DCM Operation
- Ultra-Low V_{DD} Operating Voltage for Different Output Voltage of PC Power
- V_{DD} Over-Voltage Protection
- 14V Gate Driver Clamp

Applications

- PC Power
- Server Power
- Open-Frame SMPS

Description

The highly integrated FAN6206 is a dual-channel synchronous rectification (SR) controller. FAN6206 allows design of a cost-effective power supply with fewer external components, especially suited for dual-forward topology used to obtain higher efficiency for ATX power supplies.

The primary-side control method provides synchronous rectification control for dual-forward converters that operate in continuous conduction mode (CCM). FAN6206 includes a proprietary linear-predict timing control mechanism for dual-forward converters that operate in discontinuous conduction mode (DCM) at fixed or variable frequency. PWM frequency tracking with secondary-side winding detection is provided by adding dividing resistors. The primary-side signals are generated from Fairchild's FAN6210 (Primary-Side Synchronous Rectifier Signal Trigger for Dual-Forward Converter). The primary-side signals are transferred through a pulse transformer to the secondary-side. The benefits of this technique include simple control method and improved power system reliability.

FAN6206 is available in 8-pin SOP package.

Ordering Information

Part Number Operating Temperature Range		Package	Packing Method	
FAN6206MY	-40°C to +105°C	8-Pin Small Outline Package (SOP)	Tape & Reel	

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FAN6206 — Highly Integrated Dual-Channel Synchronous Rectification Controller for Dual-Forward Converter



SP

VDD

GATE2

GND

GATE1

side to turn-on the SR gate.

respectively.

Ground

4

5

6

7

8

Driver output for freewheeling synchronous rectifier MOSFET.

Driver output for rectifying synchronous rectifier MOSFET.

Power supply pin. The threshold voltages for startup and turn-off are 8.5V and 7.5V,

Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Min.	Max.	Unit
V _{DD}	DC Supply Voltage		30	V
V _{HV}	SP, SN		30	V
VL	LPC	-0.3	7.0	V
PD	Power Dissipation at $T_A < 50^{\circ}C$		400	mW
Θ _{JA}	Junction to Ambient Thermal Resistance		130	°C/W
Ψ_{jt}	Junction to Top Thermal Characteristics		46	°C/W
TJ	Operating Junction Temperature	-40	+125	°C
T _{STG}	Storage Temperature Range	-55	+150	°C
TL	Lead Temperature, (Soldering 10 Seconds)		+260	°C
ESD	Human Body Model, JESD22-A114		4.00	k) /
	Charged Device Model, JESD22-C101		1.25	κv

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device.

2. All voltage values, except differential voltages, are given with respect to GND pin.

Recommended Operating Conditions

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to Absolute Maximum Ratings.

Symbol	Parameter	Min.	Max.	Unit
T _A	Operating Ambient Temperature	-40	+105	°C

Electrical Characteristics

 V_{DD} =20V, T_A =25°C, unless otherwise specified.

Symbol	Parameter Conditions		Min.	Тур.	Max.	Units
V _{DD} Section				ı		
V _{OP}	Continuously Operating Voltage				25	V
V _{TH-ON1}	Turn-On Threshold Voltage		8.0	8.5	9.0	V
V _{TH-ON2}	Turn-On Threshold Voltage		8.0	8.5	9.0	V
$V_{\text{TH-OFF1}}$	Turn-Off Threshold Voltage		7.0	7.5	8.0	V
V _{TH-OFF2}	Turn-Off Threshold Voltage		7.0	7.5	8.0	V
I _{DD-OP}	Operating Current	V _{DD} =15V, DET=50KHz		3	5	mA
I _{DD-ST}	Startup Current	V _{DD} = 7.5V		340	500	μA
V _{DD-OVP1}	V _{DD} Over-Voltage Protection 1		20	21	22	V
V _{DD-OVP2}	V _{DD} Over-Voltage Protection 2		20	21	22	V
VDD-OVP-HYS1	Hysteresis Voltage for V _{DD} OVP 1		1.2	1.7	2.2	V
V _{DD-OVP-HYS2}	Hysteresis Voltage for V _{DD} OVP 2		1.2	1.7	2.2	V
t _{ovp1}	V _{DD} OVP Debounce Time 1		40	60	100	μs
t _{OVP2}	V _{DD} OVP Debounce Time 2		40	60	100	μs
Output Drive	for SR MOSFET Section			•		
V _{Z1}	Output Voltage Maximum (Clamp) 1	V _{DD} = 20V		12	14	V
V _{Z2}	Output Voltage Maximum (Clamp) 2	V _{DD} = 20V		12	14	V
V _{OL1}	Output Voltage LOW 1	V _{DD} =12V, I _O =50mA			0.5	V
V _{OL2}	Output Voltage LOW 2	V _{DD} =12V, I _O =50mA			0.5	V
V _{OH1}	Output Voltage HIGH 1	V _{DD} =12V, I _O =50mA	9			V
V _{OH2}	Output Voltage HIGH 2	V _{DD} =12V, I _O =50mA	9			V
t _{R1}	Rising Time 1	V _{DD} =12V, C _L =7nF, OUT=2V~9V	30	70	120	ns
t _{R2}	Rising Time 2	V _{DD} =12V, C _L =7nF, OUT=2V~9V	30	70	120	ns
t _{F1}	Falling Time1	V _{DD} =12V, C _L =7nF, OUT=9V~2V	20	50	100	ns
t _{F2}	Falling Time 2	V _{DD} =12V, C _L =7nF, OUT=9V~2V	20	50	100	ns
V _{Z1}	Output Voltage Maximum (Clamp)	V _{DD} = 20V		12	14	V
t _{PD-HIGH-SP1}		t _R +t _{PD} , (Trigger by SP), SP-SN =5V	280	350	450	ns
t _{PD-HIGH-SP2}	Propagation Delay to OUT HIGH		280	350	450	
t _{PD-LOW-SN1}		t _R +t _{PD} ,	180	250	350	D
t _{PD-LOW-SN2}	Propagation Delay to OUT LOW	OUT LOW (Trigger by SN), SP-SN =5V		250	350	ns
t _{PD-LOW-LPC1}		t _R +t _{PD,} (Trigger by LPC)	100	150	200	ne
Shtp://www.cpc2			100	150	200	10
t _{ON-MAX1}	Maximum On Time		12	13	14	μs
t _{ON-MAX2}			12	13	14	us

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 V_{DD} =20V, T_A =25°C, unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
SP/SN Section							
V _{N-P} (turn off) 1	Threshold Voltage of V_N - V_P to Turn-Off SR MOS 1	Sweep V _{N-P-} from LOW to HIGH	3	4	5	V	
V _{N-P(turn off) 2}	Threshold Voltage of V_N - V_P to Turn-Off SR MOS 2		3	4	5	V	
VP-N(turn on) 1	Threshold Voltage of V_P - V_N to Turn-On SR MOS 1	Sweep V_{P-N-} from LOW to HIGH	3	4	5	V	
VP-N(turn on) 2	Threshold Voltage of V_P - V_N to Turn-On SR MOS 2	Sweep V_{P-N-} from LOW to HIGH	3	4	5	V	
Ratio_ _{SP-SN}	Voltage Difference between SP and SN	V _{SP} -V _{SN} / MIN(V _{SP} ,V _{SN})			5	%	
LPC Section							
Ratio_LPC-RES	Charge Divide Discharge Current Transfer Ratio vs. Input Voltage	Connect a Diode 1N4148 and Divider (Ratio 12) to LPC, $V_{DET} = 3V$, $V_{LPC} = 3V$	2.79	3.00	3.21		
V _{LPC-EN1}	LPC Enable Threshold Voltage 1		1.8	2.0	2.2	V	
V _{LPC-EN2}	LPC Enable Threshold Voltage 2		1.8	2.0	2.2	V	
VLPC-CLAMP1	Lower Clamp Voltage 1	I _{LPC} = -5μA	0.10	0.25	0.40	V	
V _{LPC-CLAMP2}	Lower Clamp Voltage 2	I _{LPC} = -5μA	0.10	0.25	0.40	V	
ILPC-SOURCE1	Maximum Source Current 1	V_{LPC} = -0.3V		250	300	μA	
ILPC-SOURCE2	Maximum Source Current 2	$V_{LPC} = -0.3V$		250	300	μA	
V _{LPC-LOW1}	Threshold Voltage for Disable LPC Function		1.3	1.5	1.7	V	
V _{LPC-LOW2}	Threshold Voltage for Disable LPC Function		1.3	1.5	1.7	V	
t _{LPC-LOW1}	Debounce Time for Disable LPC Function	V _{LPC} < V _{LPC-LOW}	70	100	130	μs	
t _{LPC-LOW2}	Debounce Time for Disable LPC Function	V _{LPC} < V _{LPC-LOW}	70	100	130	μs	

Cteristics

Typical Performance Characteristics

These characteristic graphs are normalized at $T_A = 25^{\circ}C$.



Figure 5. Turn-On Threshold Voltage 1



Figure 7. Turn-Off Threshold Voltage 1













Figure 8. Turn-Off Threshold Voltage 2



Figure 10. Startup Current









5.0

Typical Performance Characteristics

5.0

These characteristic graphs are normalized at $T_A = 25^{\circ}C$.

Function Description

Figure 29 and Figure 30 show the simplified circuit diagram of a dual-forward converter and its key waveforms. Switches Q1 and Q2 are turned on and off together. Once Q₁ and Q₂ are turned on, input voltage is applied across the transformer primary side and power is delivered to the secondary side through the transformer, powering D1. During this time, the magnetizing current linearly increases. When Q1 and Q2 are turned off, the magnetizing current of the transformer forces the reset diodes (D_{R1} and D_{R2}) and negative input voltage is applied across the transformer primary side. During this time, magnetizing current linearly decreases to zero and the secondary-side inductor current freewheels through diode D2. When synchronous rectifier SR1 and SR2 are used instead of diodes D₁ and D₂, it is important to have proper timing between drive signals for SR1 and SR2.



Figure 29. Simplified Circuit Diagram of Dual-Forward Converter





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Figure 31 shows a typical application circuit. When a dual-forward converter operates in continuous conduction mode, the SR gate signals (GATE1 and GATE2) are mainly controlled by SP and SN signals. SP and SN signals are transferred through a pulse transformer from XP and XN signals, which are generated by FAN6210 (Primary-Side Synchronous Rectifier Signal Trigger for Dual Forward Converter).



Figure 31. Typical Application Circuit

Figure 32 shows the timing diagram for continuous conduction mode (CCM). Figure 33 shows the timing diagram for discontinuous conduction mode (DCM).

The switching operation of SR MOSFETs Q_3 and Q_4 is determined by the SN and SP signals. FAN6206 turns on SR MOSFETs at the rising edge of the SP signal, while it turns off the SR MOSFETs at the rising edge of the SN signal. Within one switching cycle, SP and SN are obtained two times.

With a voltage divider R_1 and R_2 connected from LPC1 to secondary winding, R_3 and R_4 connected from LPC2 to secondary winding, the PWM timing sequences and frequency can be tracked precisely. The SR MOSFET is turned on by SP signal only when the voltage level on LPC1 or LPC2 pin is pulled LOW to GND.

During PWM-on period, the rectifying SR Q_3 is turned on by the rising edge of the SP signal after a propagation delay ($t_{PD-HIGH-SP1}$) and Q_3 is turned off by the rising edge of the SN signal after a propagation delay ($t_{PD-LOW-SN1}$). During PWM-off period, the freewheeling SR Q_4 is turned on by the rising edge of the SP signal after a propagation delay ($t_{PD-HIGH-SP2}$) and Q_4 is turned off by the rising edge of the SN signal after a propagation delay ($t_{PD-LOW-SN2}$) in CCM operation.

In DCM operation, the proprietary Linear-Predict Timing Control (LPC) technique can provide synchronous rectification control mechanism for freewheeling SR MOSFET. Since SN signal is sent following with PWM signal, the freewheeling SR MOSFET cannot be turned off in time by SN signal before I_{Lo} linearly decreases to zero. Therefore, the LPC mechanism is applied to turn off Q₃ in DCM mode.



Linear-Predict Timing Control

When a dual-forward converter operates in CCM or DCM; in PWM ton period, the VIN voltage is applied to the primary winding and the secondary inductor starts to rise linearly and store energy. The across voltage on secondary winding is coupled from primary winding and proportional to VIN. The SR controller can detect this winding voltage through a voltage divider and acquire the VIN level. According to this detected VIN level during PWM turn-on period, SR controller produces a charge current I_{CHG} to charge internal capacitor, CT, of the SR controller. On the other hand, at PWM turn-off period, the energy stored in the secondary inductor is discharged. The SR controller also detects the output voltage level to modulate discharge current IDISCHG of internal capacitor, CT. Once the internal capacitor voltage reaches zero, SR controller turns off SR MOS immediately.

R₄ is connected between the LPC2 pin and the drain terminal of Q₄. During PWM turn-on period, voltage on the LPC2 pin is pulled HIGH due to the secondary winding coupled from primary winding. At this moment, SR MOS is turned off and the internal body diode of SR MOS is reverse-biased. During PWM turn-off period, the potential on the primary winding reverses and the internal body diode starts to conduct output current. The voltage on the LPC2 pin is also pulled LOW to GND. R₂ is recommended as 10kΩ and the divided voltage level on the LPC1 pin is suggested between 3V~5V. If the voltage level of V₀ is 12V, the resistor values are recommended as 105kΩ for R₃ and 10kΩ for R₄. The

turn-off timing of Q_4 is determined by the ratio $\frac{R_4}{R_3 + R_4}$

as Figure 34 shows. If $\frac{R_4}{R_3 + R_4}$ decreases, Q₄ is turned

off earlier.



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Under-Voltage Lockout (UVLO)

The power-on and off thresholds are fixed at 8.5V and 7.5V. The VDD pin is connected to a 12V output voltage terminal.

VDD Pin Over-Voltage Protection

The over-voltage conditions are usually caused by open feedback loops. V_{DD} over-voltage protection is built in to prevent damage if over voltage occurs. When the voltage on the VDD pin exceeds 21V, the SR controller turns off all of SR MOS operations.







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